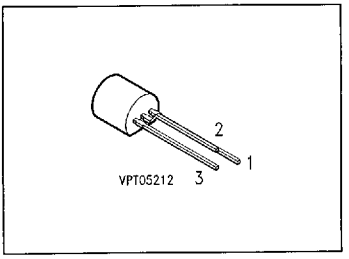
SIEMENS

PNP Silicon RF Transistor

BF 606 A

- For VHF oscillator stages



Type	Marking	Ordering Code	Pin Configuration 1	2	3	Package[1]
BF 606 A	–	Q62702-F535	C	E	B	TO-92

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE0}	30	V
Collector-base voltage	V_{CB0}	40	
Emitter-base voltage	V_{EB0}	4	
Collector current	I_C	25	mA
Emitter current	I_E	30	
Total power dissipation, $T_A \leq 45$ °C	P_{tot}	300	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	– 55 ... + 150	

Thermal Resistance

Junction - ambient	$R_{th\,JA}$	≤ 350	K/W

1) For detailed information see chapter Package Outlines.

Electrical Characteristics
at T_A = 25 °C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 2 mA	$V_{(BR)\,CE0}$	30	–	–	V
Collector-base breakdown voltage I_C = 10 µA	$V_{(BR)\,CB0}$	40	–	–	
Emitter-base breakdown voltage I_E = 10 µA	$V_{(BR)\,EB0}$	4	–	–	
Collector cutoff current V_{CB} = 20 V	I_{CB0}	–	–	60	nA
DC current gain I_C = 1 mA, V_{CE} = 10 V	h_{FE}	30	–	–	–
AC Characteristics					
Transition frequency I_C = 5 mA, V_{CE} = 10 V, f = 100 MHz	f_T	–	700	–	MHz
Collector-emitter capacitance V_{CE} = 10 V, V_{BE} = 0 V, f = 1 MHz	C_{ce}	–	0.35	–	pF
Collector-base capacitance V_{CB} = 10 V, V_{BE} = 0 V, f = 1 MHz	C_{cb}	–	–	0.85	